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STB80NF03L-04T4

N-channel 30 V, 0.0035 Ω , 80 A D²PAK
STripFET™ II Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STB80NF03L-04T4	30 V	< 0.004 Ω	80 A

- Exceptional dv/dt capability
- 100% avalanche tested
- Low threshold drive

Application

- Switching applications

Description

This Power MOSFET is the latest development of STMicroelectronics unique “single feature size” strippased process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

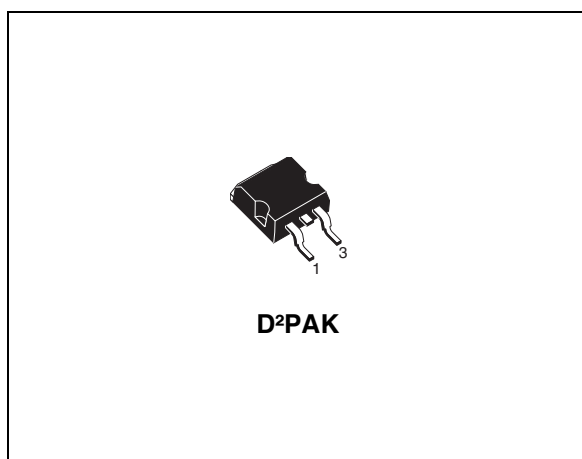


Figure 1. Internal schematic diagram

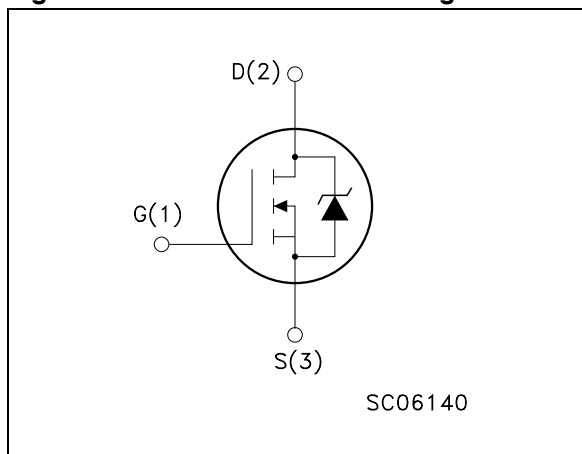


Table 1. Device summary

Order code	Marking	Package	Packaging
STB80NF03L-04T4	80NF03L-04	D ² PAK	Tape and reel

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Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	2	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	2.3	J
T_{stg} T_j	Storage temperature Operating junction temperature	-60 to 175	$^\circ\text{C}$

1. Limited by package
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 80\text{ A}$, $di/dt \leq 240\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq T_{JMAX}$
4. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 80\text{ A}$, $V_{DD} = 50\text{ V}$

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Electrical characteristics

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2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 250 μA, V _{GS} = 0	30			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = max rating V _{DS} = max rating @125 °C			1 10	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ±20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1			V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 40 A V _{GS} = 4.5 V, I _D = 40 A		0.0035 0.004	0.004 0.0055	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} = 15 V, I _D = 15 A	-	50		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	5500 1670 290		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 24 V, I _D = 80 A, V _{GS} = 4.5 V <i>Figure 15</i>	-	85 23 40	110	nC nC nC

1. Pulsed: pulse duration = 300 μs, duty cycle 1.5%

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Electrical characteristics

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 4.5\text{ V}$ <i>Figure 16</i>	-	30	-	ns
t_r	Rise time			270		ns
$t_{d(off)}$	Turn-off-delay time			110		ns
t_f	Fall time			95		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 80\text{ A}$, $V_{DD} = 20\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ $T_j = 150\text{ }^\circ\text{C}$	-	75		ns
Q_{rr}	Reverse recovery charge			0.15		μC
I_{RRM}	Reverse recovery current			4		A

1. Pulse width limited by safe operating area

2. Pulse duration=300 μs , duty cycle 1.5%

Electrical characteristics

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2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

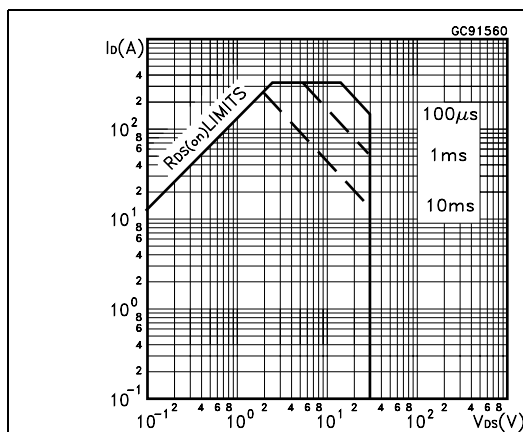


Figure 3. Thermal impedance

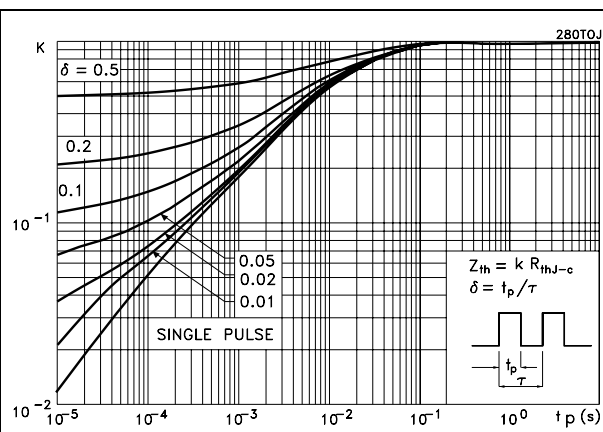


Figure 4. Output characteristics

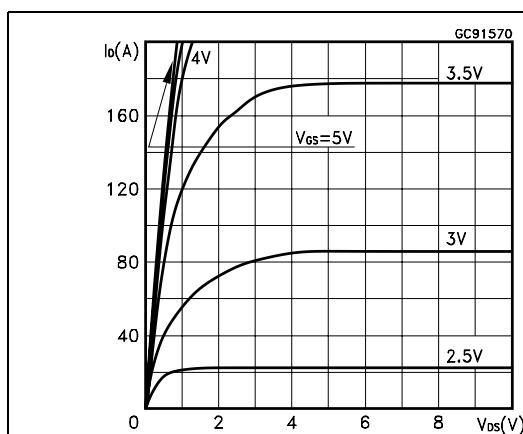


Figure 5. Transfer characteristics

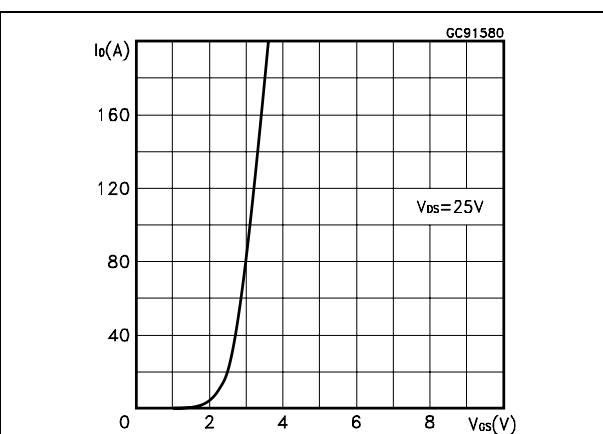


Figure 6. Transconductance

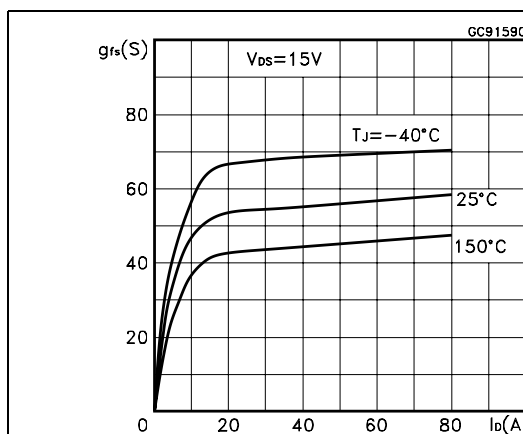
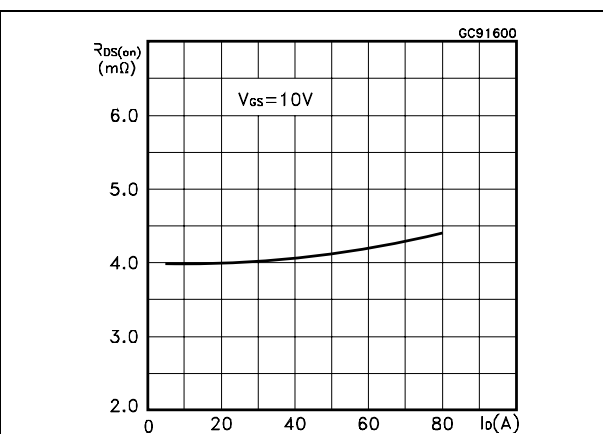


Figure 7. Static drain-source on resistance



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Electrical characteristics

Figure 8. Gate charge vs. gate-source voltage

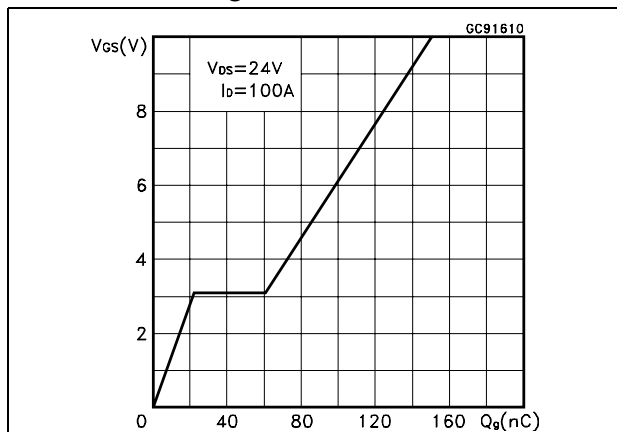


Figure 9. Capacitance variations

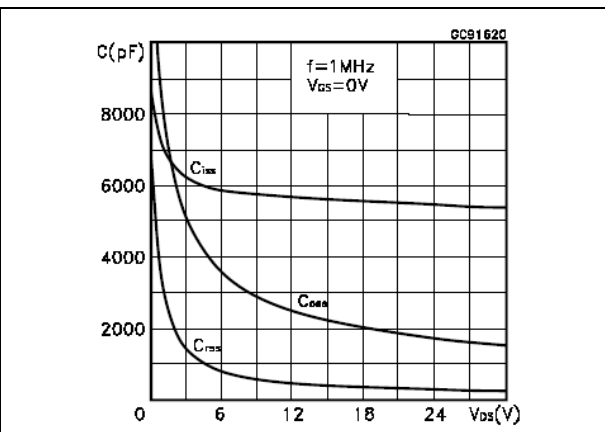


Figure 10. Normalized gate threshold voltage vs. temperature

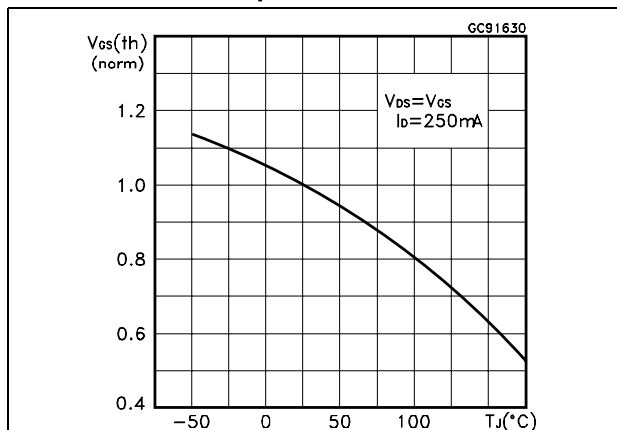


Figure 11. Normalized on resistance vs. temperature

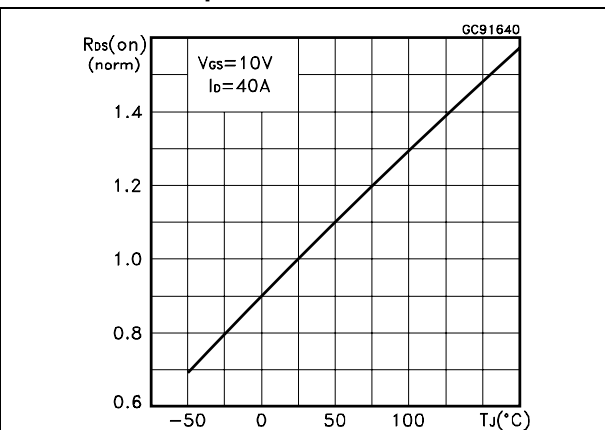


Figure 12. Source-drain diode forward characteristics

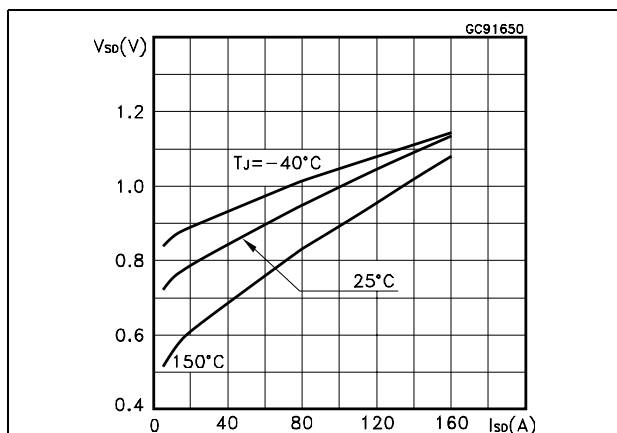
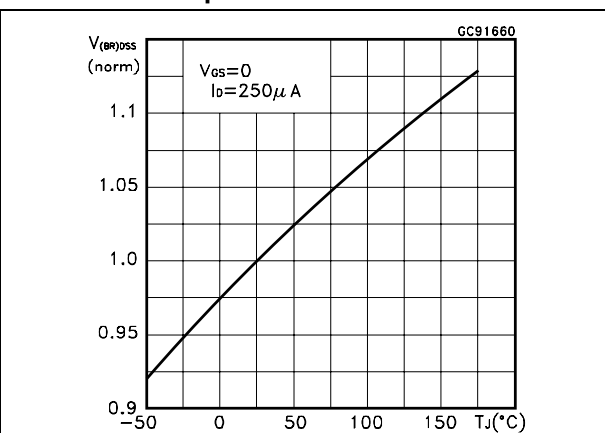


Figure 13. Normalized breakdown voltage vs temperature.



Test circuits

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3 Test circuits

Figure 14. Switching times test circuit for resistive load

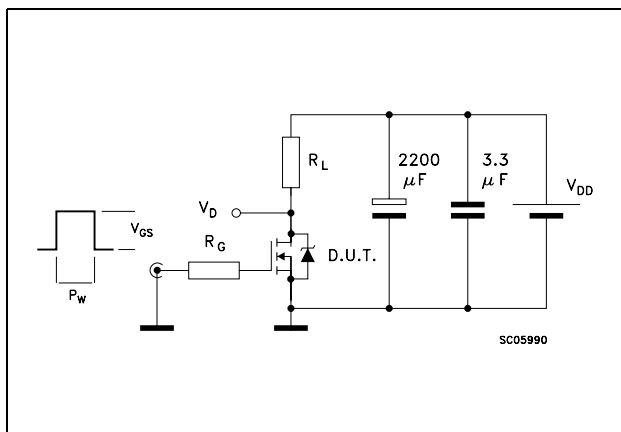


Figure 15. Gate charge test circuit

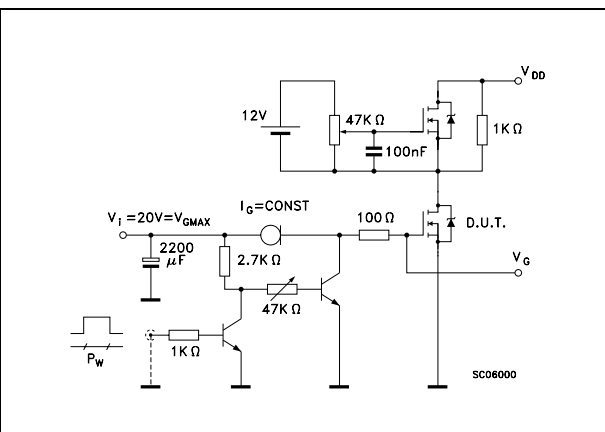


Figure 16. Test circuit for inductive load switching and diode recovery times

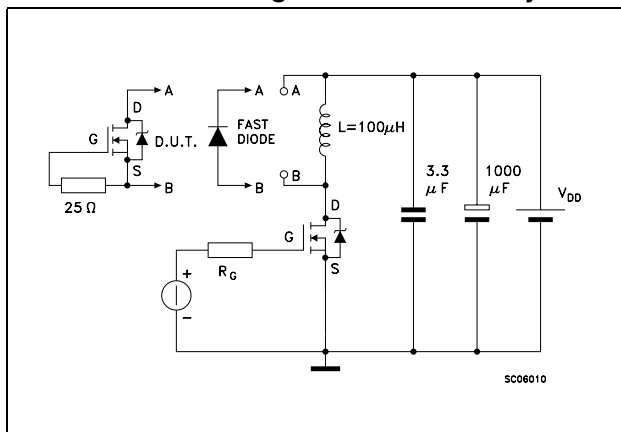


Figure 17. Unclamped inductive load test circuit

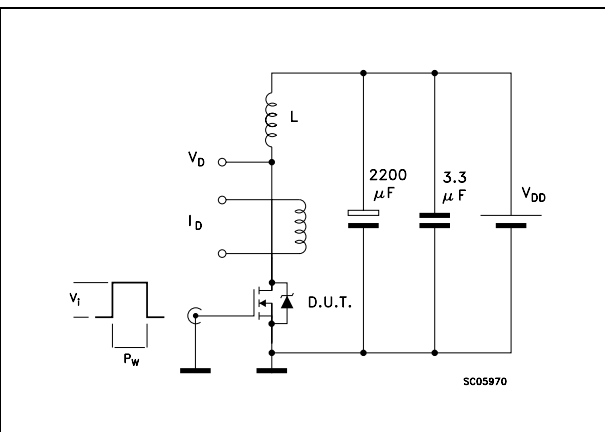


Figure 18. Unclamped inductive waveform

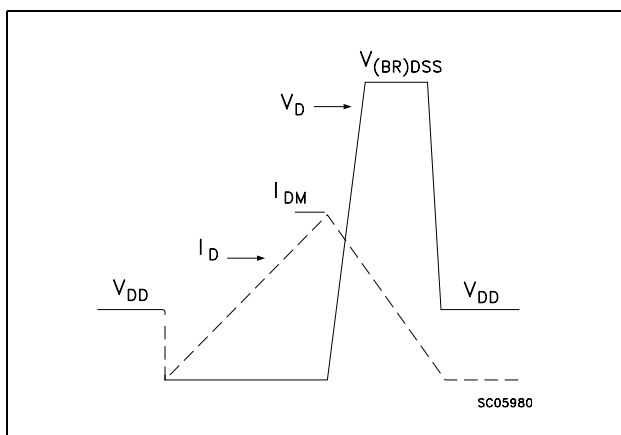
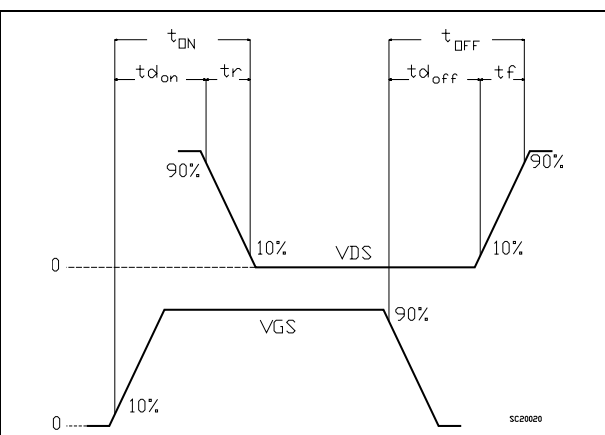


Figure 19. Switching time waveform



4 Package mechanical data

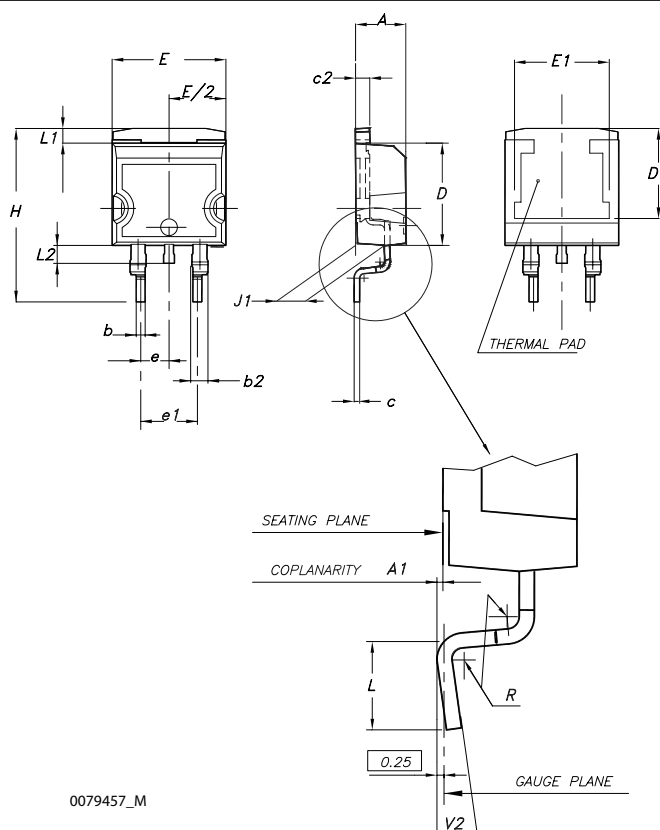
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Package mechanical data

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D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



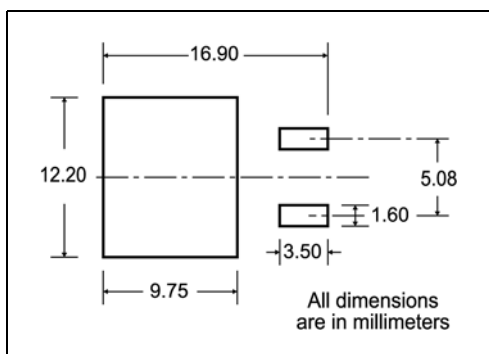
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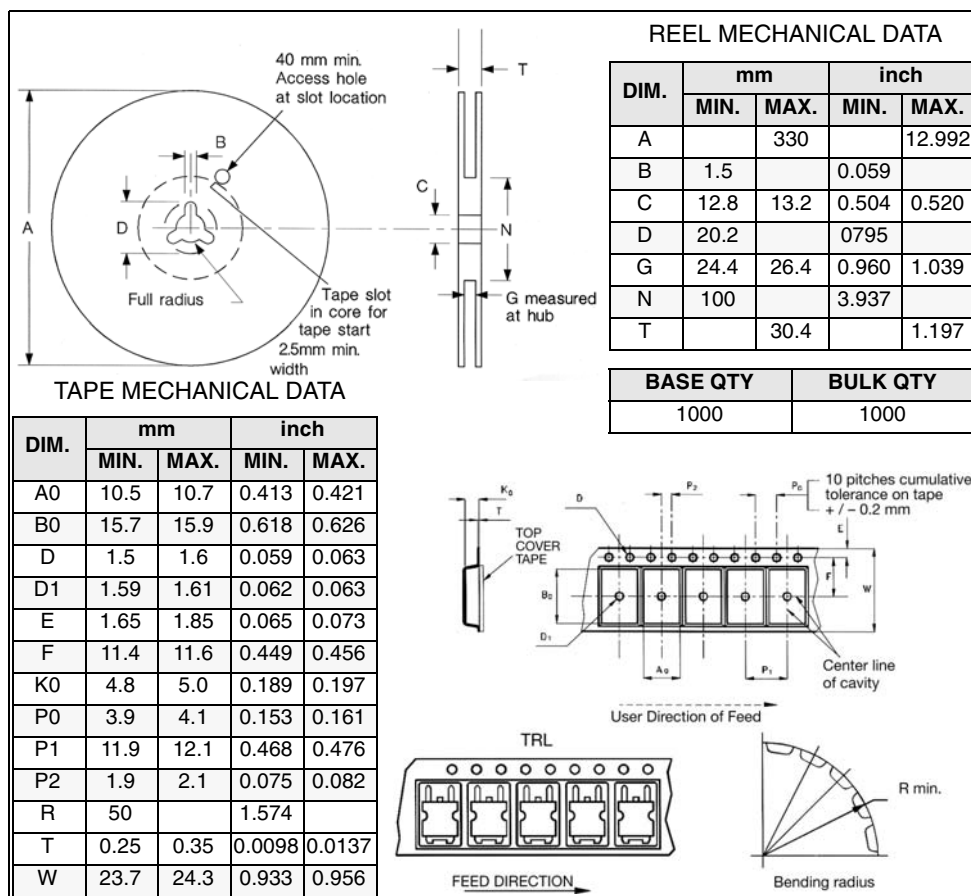
Packaging mechanical data

5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

Revision history

STB80NF03L-04T4

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
02-Oct-2007	3	Initial electronic version
20-Apr-2009	4	Removed packages TO-220, I ² PAK.

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